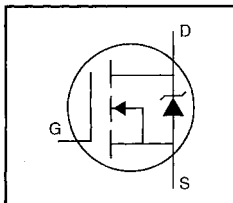


## HEXFET® Power MOSFET

- Dynamic  $dv/dt$  Rating
- Repetitive Avalanche Rated
- Logic-Level Gate Drive
- $R_{DS(on)}$  Specified at  $V_{GS}=4V$  &  $5V$
- $175^{\circ}C$  Operating Temperature
- Fast Switching
- Ease of Paralleling



$$V_{DSS} = 100V$$

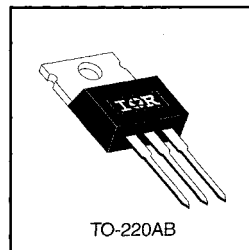
$$R_{DS(on)} = 0.54\Omega$$

$$I_D = 5.6A$$

## Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



TO-220AB

DATA  
SHEETS

## Absolute Maximum Ratings

|                              | Parameter                                           | Max.                  | Units          |
|------------------------------|-----------------------------------------------------|-----------------------|----------------|
| $I_D$ @ $T_C = 25^{\circ}C$  | Continuous Drain Current, $V_{GS}$ @ 5.0 V          | 5.6                   | A              |
| $I_D$ @ $T_C = 100^{\circ}C$ | Continuous Drain Current, $V_{GS}$ @ 5.0 V          | 4.0                   |                |
| $I_{DM}$                     | Pulsed Drain Current ①                              | 18                    |                |
| $P_D$ @ $T_C = 25^{\circ}C$  | Power Dissipation                                   | 43                    | W              |
|                              | Linear Derating Factor                              | 0.29                  | W/ $^{\circ}C$ |
| $V_{GS}$                     | Gate-to-Source Voltage                              | $\pm 10$              | V              |
| $E_{AS}$                     | Single Pulse Avalanche Energy ②                     | 100                   | mJ             |
| $I_{AR}$                     | Avalanche Current ①                                 | 5.6                   | A              |
| $E_{AR}$                     | Repetitive Avalanche Energy ①                       | 4.3                   | mJ             |
| $dv/dt$                      | Peak Diode Recovery $dv/dt$ ③                       | 5.5                   | V/ns           |
| $T_J$<br>$T_{STG}$           | Operating Junction and<br>Storage Temperature Range | -55 to +175           | $^{\circ}C$    |
|                              | Soldering Temperature, for 10 seconds               | 300 (1.6mm from case) |                |
|                              | Mounting Torque, 6-32 or M3 screw                   | 10 lbf•in (1.1 N•m)   |                |

## Thermal Resistance

|                 | Parameter                           | Min. | Typ. | Max. | Units         |
|-----------------|-------------------------------------|------|------|------|---------------|
| $R_{\theta JC}$ | Junction-to-Case                    | —    | —    | 3.5  | $^{\circ}C/W$ |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface | —    | 0.50 | —    |               |
| $R_{\theta JA}$ | Junction-to-Ambient                 | —    | —    | 62   |               |

Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

|                                 | Parameter                            | Min. | Typ. | Max. | Units               | Test Conditions                                                     |
|---------------------------------|--------------------------------------|------|------|------|---------------------|---------------------------------------------------------------------|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | 100  | —    | —    | V                   | $V_{GS}=0V$ , $I_D=250\mu A$                                        |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.12 | —    | V/ $^\circ\text{C}$ | Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$                  |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | —    | 0.54 | $\Omega$            | $V_{GS}=5.0V$ , $I_D=3.4A$ ④                                        |
|                                 |                                      | —    | —    | 0.76 |                     | $V_{GS}=4.0V$ , $I_D=2.8A$ ④                                        |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | 1.0  | —    | 2.0  | V                   | $V_{DS}=V_{GS}$ , $I_D=250\mu A$                                    |
| $g_{fs}$                        | Forward Transconductance             | 1.9  | —    | —    | S                   | $V_{DS}=50V$ , $I_D=3.4A$ ④                                         |
| $I_{OSS}$                       | Drain-to-Source Leakage Current      | —    | —    | 25   | $\mu A$             | $V_{DS}=100V$ , $V_{GS}=0V$                                         |
|                                 |                                      | —    | —    | 250  |                     | $V_{DS}=80V$ , $V_{GS}=0V$ , $T_J=150^\circ\text{C}$                |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —    | 100  | nA                  | $V_{GS}=10V$                                                        |
|                                 | Gate-to-Source Reverse Leakage       | —    | —    | -100 |                     | $V_{GS}=-10V$                                                       |
| $Q_g$                           | Total Gate Charge                    | —    | —    | 6.1  | nC                  | $I_D=5.6A$                                                          |
| $Q_{GS}$                        | Gate-to-Source Charge                | —    | —    | 2.6  |                     | $V_{DS}=80V$                                                        |
| $Q_{gd}$                        | Gate-to-Drain ("Miller") Charge      | —    | —    | 3.3  |                     | $V_{GS}=5.0V$ See Fig. 6 and 13 ④                                   |
| $t_{d(on)}$                     | Turn-On Delay Time                   | —    | 9.3  | —    | ns                  | $V_{DD}=50V$                                                        |
| $t_r$                           | Rise Time                            | —    | 47   | —    |                     | $I_D=5.6A$                                                          |
| $t_{d(off)}$                    | Turn-Off Delay Time                  | —    | 16   | —    |                     | $R_G=12\Omega$                                                      |
| $t_f$                           | Fall Time                            | —    | 18   | —    |                     | $R_D=8.4\Omega$ See Figure 10 ④                                     |
| $L_D$                           | Internal Drain Inductance            | —    | 4.5  | —    | nH                  | Between lead, 6 mm (0.25in.) from package and center of die contact |
| $L_S$                           | Internal Source Inductance           | —    | 7.5  | —    |                     |                                                                     |
| $C_{iss}$                       | Input Capacitance                    | —    | 250  | —    | pF                  | $V_{GS}=0V$                                                         |
| $C_{oss}$                       | Output Capacitance                   | —    | 80   | —    |                     | $V_{DS}=25V$                                                        |
| $C_{rss}$                       | Reverse Transfer Capacitance         | —    | 15   | —    |                     | $f=1.0\text{MHz}$ See Figure 5                                      |



## Source-Drain Ratings and Characteristics

|          | Parameter                              | Min.                                                                      | Typ. | Max. | Units   | Test Conditions                                                                                                                                   |
|----------|----------------------------------------|---------------------------------------------------------------------------|------|------|---------|---------------------------------------------------------------------------------------------------------------------------------------------------|
| $I_S$    | Continuous Source Current (Body Diode) | —                                                                         | —    | 5.6  | A       | MOSFET symbol showing the integral reverse p-n junction diode.  |
| $I_{SM}$ | Pulsed Source Current (Body Diode) ①   | —                                                                         | —    | 18   |         |                                                                                                                                                   |
| $V_{SD}$ | Diode Forward Voltage                  | —                                                                         | —    | 2.5  | V       | $T_J=25^\circ\text{C}$ , $I_S=5.6A$ , $V_{GS}=0V$ ④                                                                                               |
| $t_{rr}$ | Reverse Recovery Time                  | —                                                                         | 110  | 130  | ns      | $T_J=25^\circ\text{C}$ , $I_F=5.6A$                                                                                                               |
| $Q_{rr}$ | Reverse Recovery Charge                | —                                                                         | 0.50 | 0.65 | $\mu C$ | $di/dt=100A/\mu s$ ④                                                                                                                              |
| $t_{on}$ | Forward Turn-On Time                   | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ ) |      |      |         |                                                                                                                                                   |

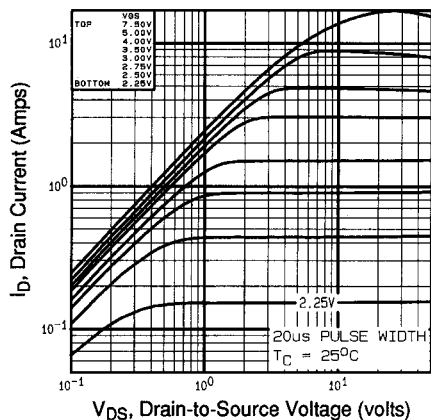
## Notes:

① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)

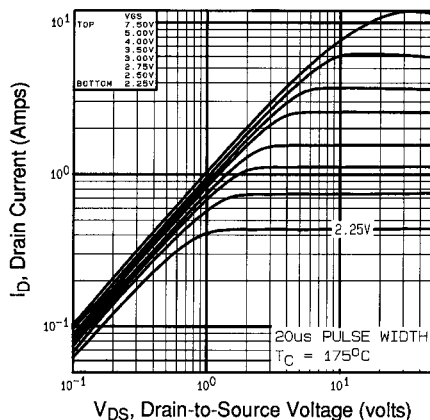
③  $I_{SD} \leq 5.6A$ ,  $di/dt \leq 75A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$

②  $V_{DD}=25V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=4.8\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=5.6A$  (See Figure 12)

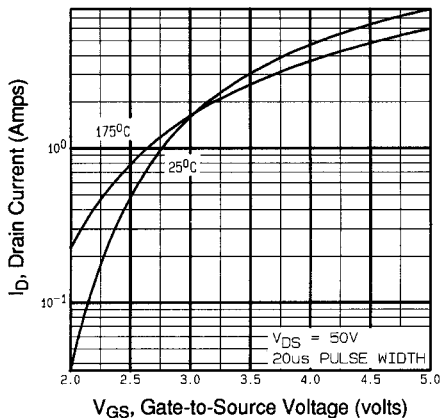
④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



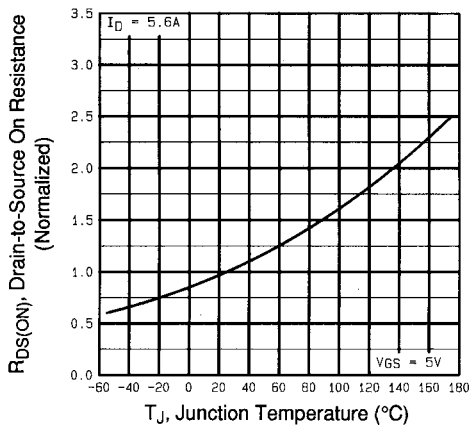
**Fig 1.** Typical Output Characteristics,  
 $T_C = 25^\circ\text{C}$



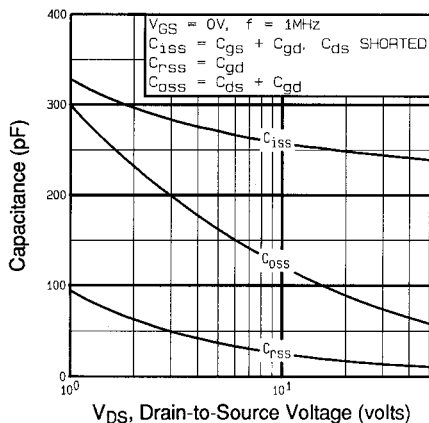
**Fig 2.** Typical Output Characteristics,  
 $T_C = 175^\circ\text{C}$



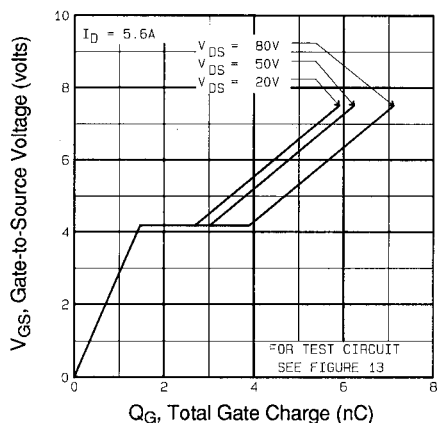
**Fig 3.** Typical Transfer Characteristics



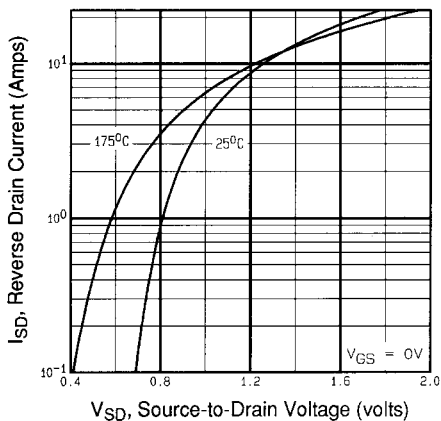
**Fig 4.** Normalized On-Resistance  
Vs. Temperature



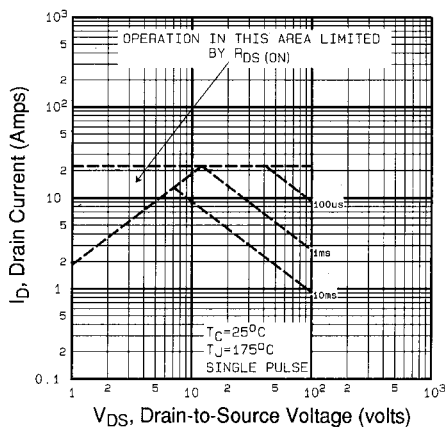
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



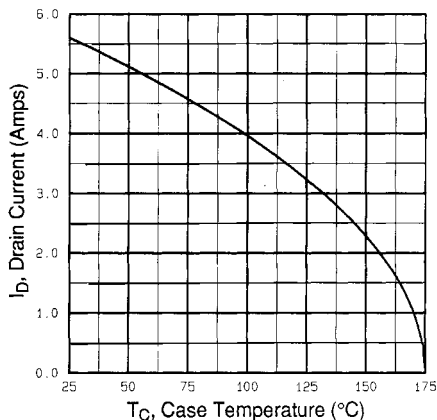
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



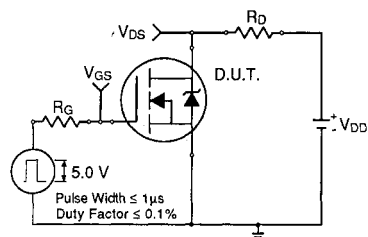
**Fig 7.** Typical Source-Drain Diode Forward Voltage



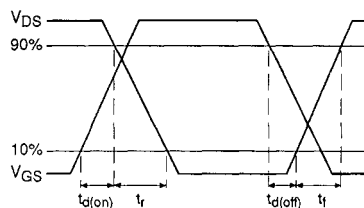
**Fig 8.** Maximum Safe Operating Area



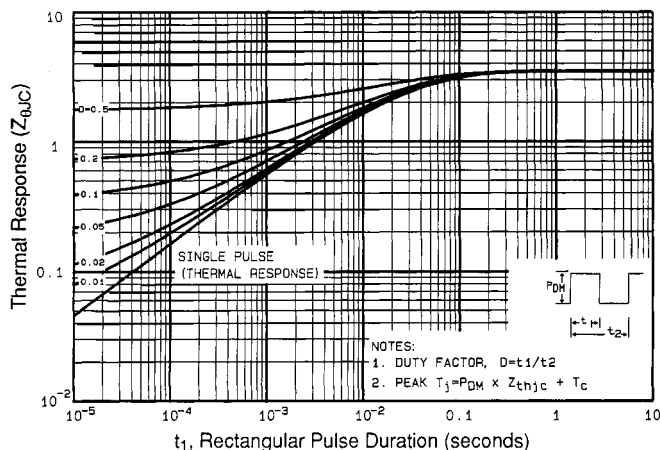
**Fig 9.** Maximum Drain Current Vs. Case Temperature



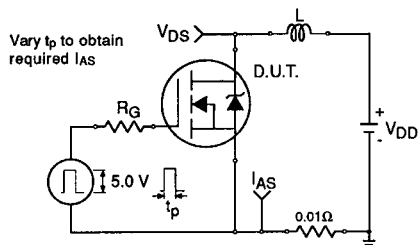
**Fig 10a.** Switching Time Test Circuit



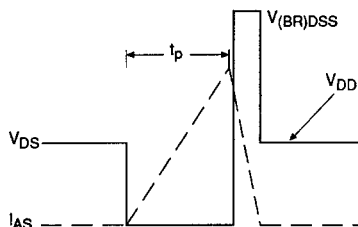
**Fig 10b.** Switching Time Waveforms



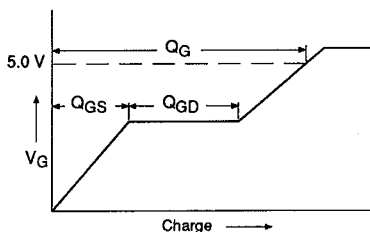
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



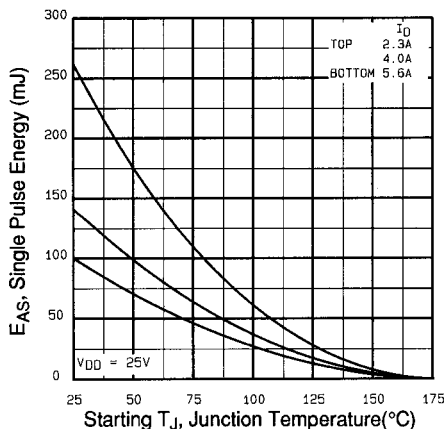
**Fig 12a.** Unclamped Inductive Test Circuit



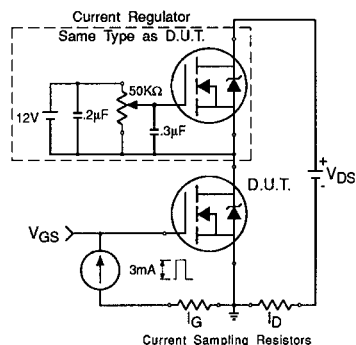
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

**Appendix A:** Figure 14, Peak Diode Recovery  $dv/dt$  Test Circuit – See page 1505

**Appendix B:** Package Outline Mechanical Drawing – See page 1509

**Appendix C:** Part Marking Information – See page 1516

**Appendix E:** Optional Leadforms – See page 1525

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